

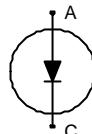
Fast switching diode chip in EMCON-Technology

FEATURES:

- 1200V EMCON technology 120 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- EUPEC power modules and discrete devices



Applications:

- SMPS, resonant applications, drives

Chip Type	V _{CE}	I _{cn}	Die Size	Package	Ordering Code
SIDC14D120H	1200V	30A	3.80 x 3.80 mm ²	sawn on foil	Q67050-A4096-A001

MECHANICAL PARAMETER:

Raster size	3.80 x 3.80	mm ²
Area total / active	14.44 / 9.80	
Anode pad size	2.38 x 2.38	
Thickness	120	µm
Wafer size	125	mm
Flat position	180	deg
Max. possible chips per wafer	704	
Passivation frontside	Photoimide	
Anode metalization	3200 nm Al Si 1%	
Cathode metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	tbd	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

Maximum Ratings

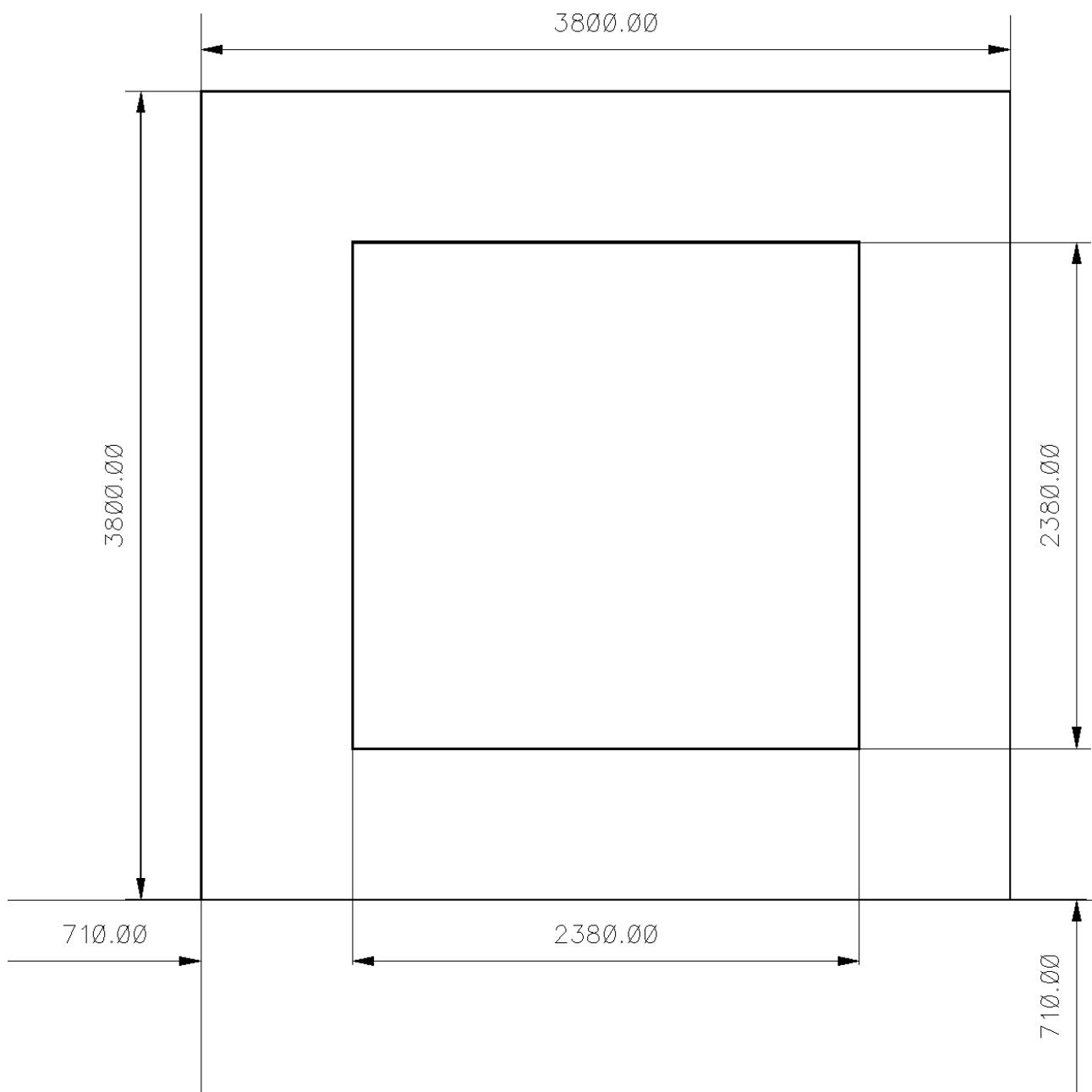
Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		1200	V
Continous forward current limited by T_{jmax}	I_F		30	
Single pulse forward current (depending on wire bond configuration)	I_{FSM}	$t_P = 10 \text{ ms sinusoidal}$	tbd	A
Maximum repetitive forward current limited by T_{jmax}	I_{FRM}		60	
Operating junction and storage temperature	T_j, T_{stg}		-55...+150	°C

Static Electrical Characteristics (tested on chip), $T_j=25 \text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Reverse leakage current	I_R	$V_R=1200V$			250	µA
Cathode-Anode breakdown Voltage	V_{Br}	$I_R=4mA$	$T_j=25 \text{ °C}$	1200		V
Forward voltage drop	V_F	$I_F=(25)30A$	$T_j=25 \text{ °C}$		(1.6)1.8	V

Dynamic Electrical Characteristics, at $T_j = 25 \text{ °C}$, unless otherwise specified, tested at component

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Reverse recovery time	t_{rr1}	$I_F=30A$	$T_j = 25 \text{ °C}$		tbd	
	t_{rr2}	$di/dt= tbd \text{ A/ms}$ $V_R=600V$	$T_j = 150 \text{ °C}$			ns
Peak recovery current	I_{RRM1}	$I_F=30A$	$T_j = 25 \text{ °C}$		tbd	
	I_{RRM2}	$di/dt= tbd \text{ A/ms}$ $V_R=600V$	$T_j = 150 \text{ °C}$			A
Reverse recovery charge	Q_{rr1}	$I_F=30A$	$T_j=25 \text{ °C}$		tbd	
	Q_{rr2}	$di/dt= tbd \text{ A/ms}$ $V_R=600V$	$T_j=150 \text{ °C}$			nC
Peak rate of fall of reverse recovery current	di_{rr1}/dt	$I_F=30A$	$T_j=25 \text{ °C}$		tbd	
	di_{rr2}/dt	$di/dt= tbd \text{ A/ms}$ $V_R=600V$	$T_j=150 \text{ °C}$			A/µs
Softness	$S1$	$I_F=30A$	$T_j=25 \text{ °C}$		tbd	
	$S2$	$di/dt= tbd \text{ A/ms}$ $V_R=600V$	$T_j=150 \text{ °C}$			1

CHIP DRAWING:



Preliminary

SIDC14D120H

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the
device data sheet

INFINEON TECHNOLOGIES /
EUPEC

tbd

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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